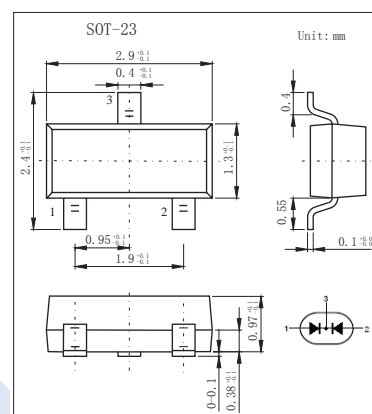


## Switching Diodes

## 1SS184

## ■ Features

- Small Package
- Low forward voltage : $V_{F(3)} = 0.9\text{ V(Typ.)}$
- Fast Reverse Recovery Time : $t_{rr} = 1.6\text{ ns(Typ.)}$
- Small Total Capacitance : $C_T = 0.9\text{ pF(Typ.)}$

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Peak Reverse voltage	$V_{RM}$	85	V
DC Blocking Voltage	$V_R$	80	
Average Rectified Output Current	$I_o$	100	mA
Peak forward surge current	$I_{FM}$	300	
Power Dissipation	$P_D$	150	mW
Junction Temperature	$T_J$	125	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	$V_R$	$I_R = 100\text{ }\mu\text{A}$	80			V
Forward voltage	$V_{F1}$	$I_F = 1\text{ mA}$		0.6		
	$V_{F2}$	$I_F = 10\text{ mA}$		0.72		
	$V_{F3}$	$I_F = 100\text{ mA}$		0.9	1.2	
Reverse voltage leakage current	$I_{R1}$	$V_R = 30\text{ V}$			0.1	$\mu\text{A}$
	$I_{R2}$	$V_R = 80\text{ V}$			0.5	
Capacitance between terminals	$C_T$	$V_R = 0\text{ V}, f = 1\text{ MHz}$		0.9	3	pF
Reverse recovery time	$t_{rr}$	$I_F = 10\text{ mA}$		1.6	4	ns

## ■ Marking

Marking	B3
---------	----

## Switching Diodes

## 1SS184

## ■ Typical Characteristics

